

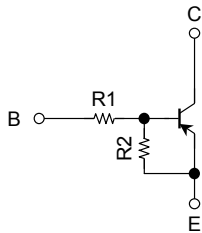
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process) (Bias Resistor Built-in Transistor)

## RN2901FE, RN2902FE, RN2903FE RN2904FE, RN2905FE, RN2906FE

Switching, Inverter Circuit, Interface Circuit and  
Driver Circuit Applications

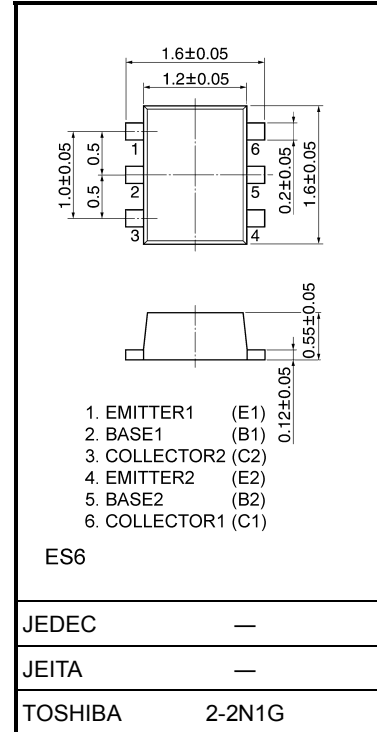
- Two devices are incorporated into an Extreme-Super-Mini (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count.  
Reducing the parts count enables the manufacture of ever more compact equipment and lowers assembly cost.
- Complementary to RN1901FE~RN1906FE

### Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2901FE	4.7	4.7
RN2902FE	10	10
RN2903FE	22	22
RN2904FE	47	47
RN2905FE	2.2	47
RN2906FE	4.7	47

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-2N1G

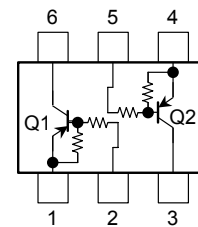
Weight: 0.003 g (typ.)

### Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-10	V
		-5	
Collector current	$I_C$	-100	mA
Collector power dissipation	$P_C$ (Note)	100	mW
Junction temperature	$T_j$	150	°C
Storage temperature range	$T_{stg}$	-55~150	°C

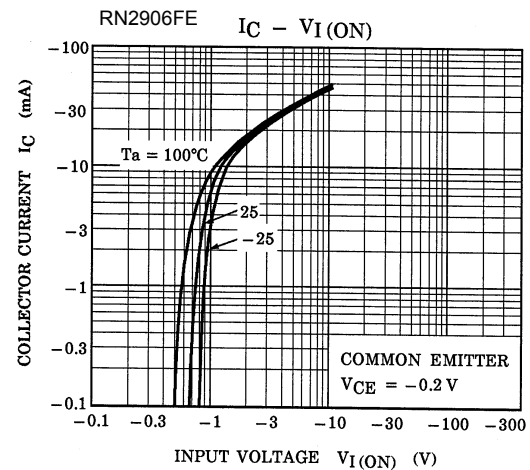
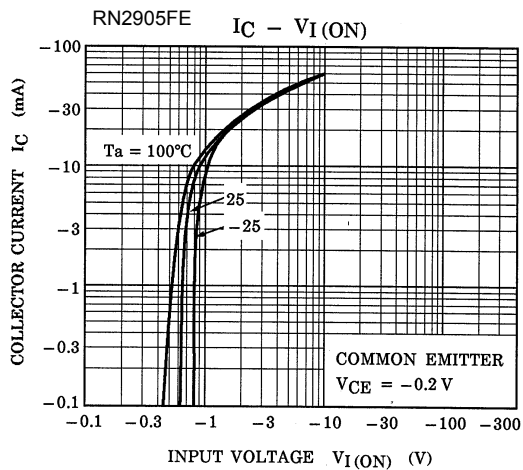
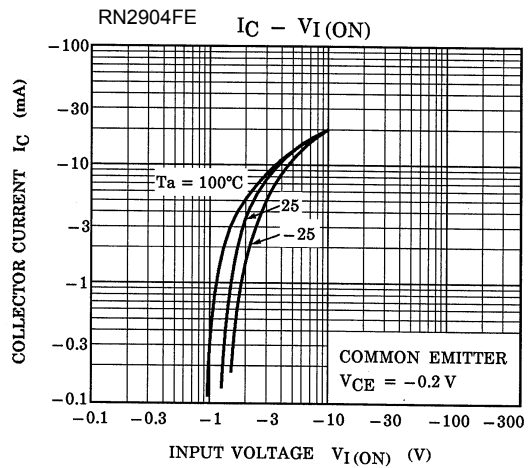
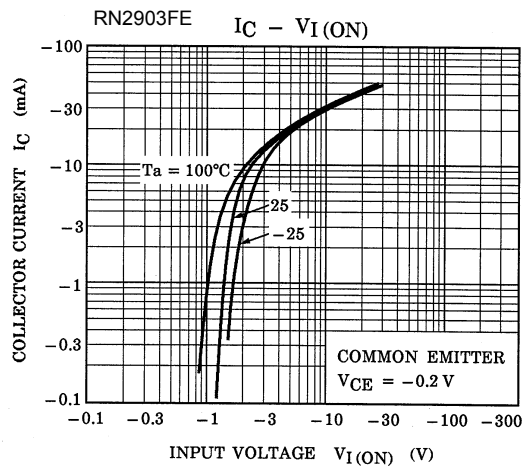
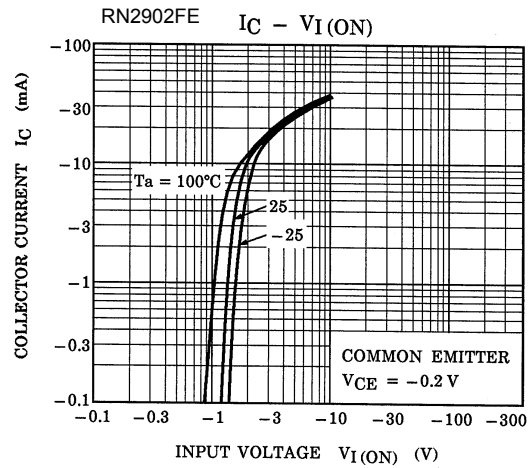
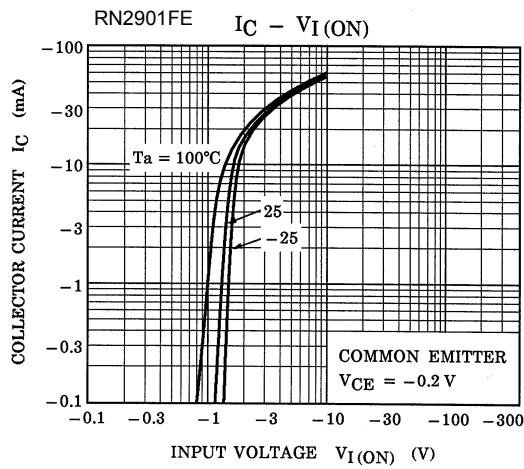
Note: Total rating

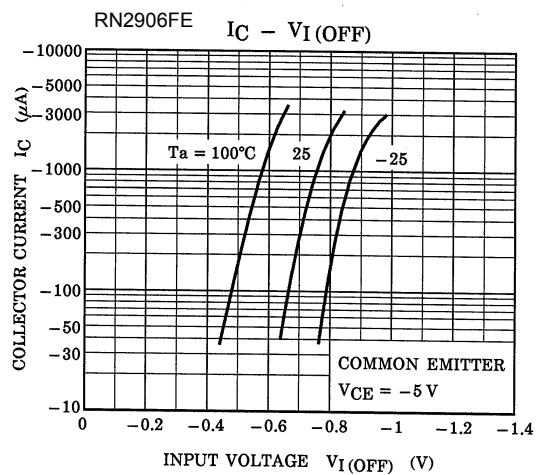
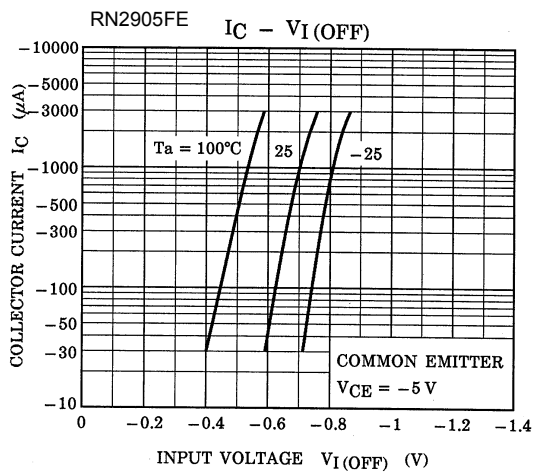
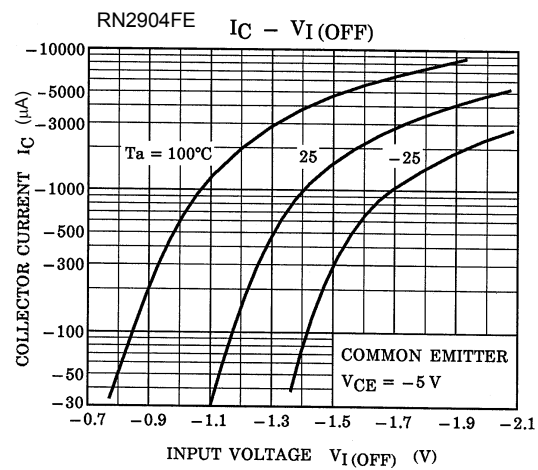
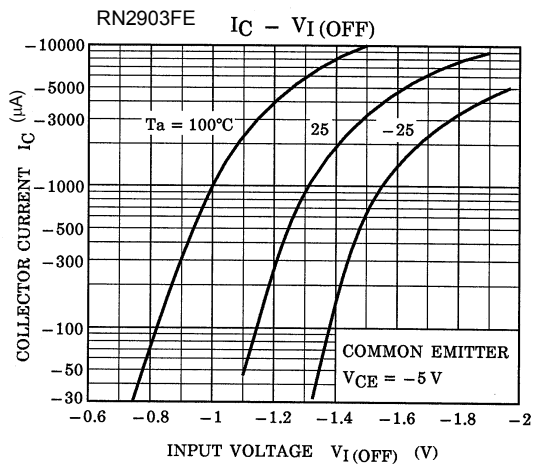
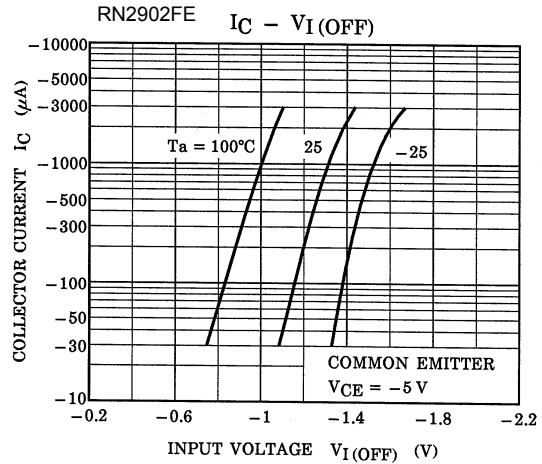
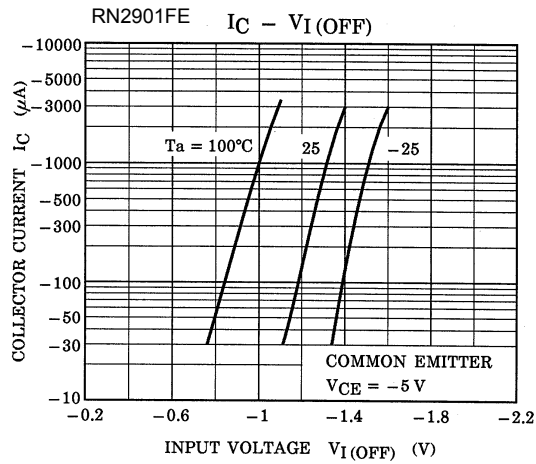
### Equivalent Circuit (top view)

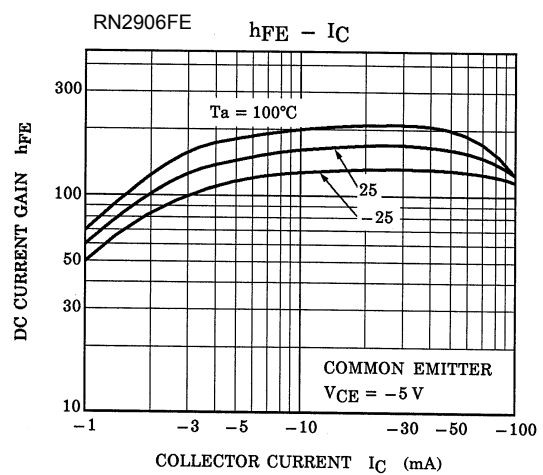
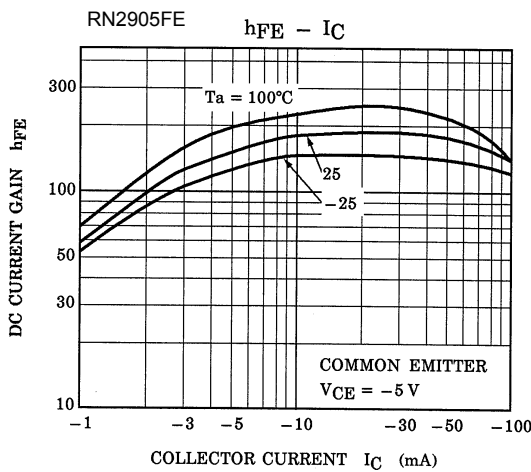
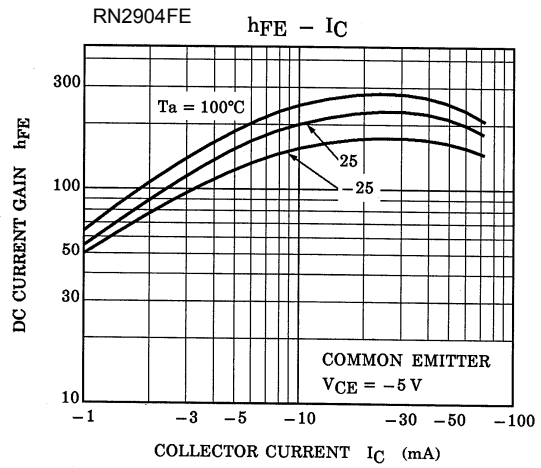
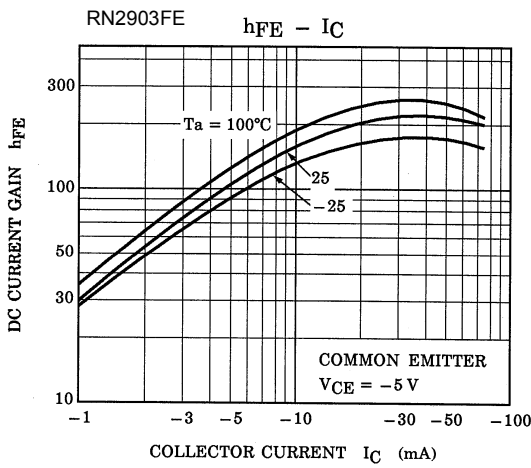
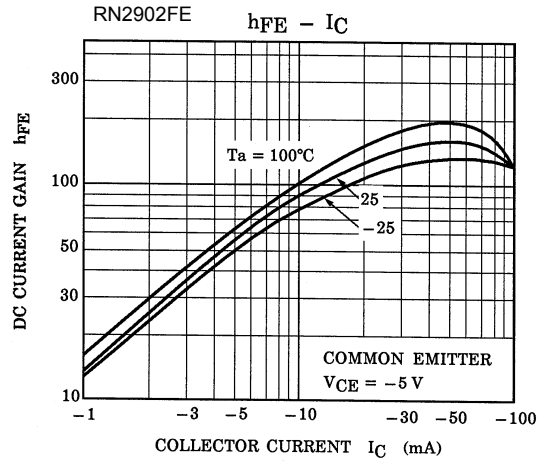
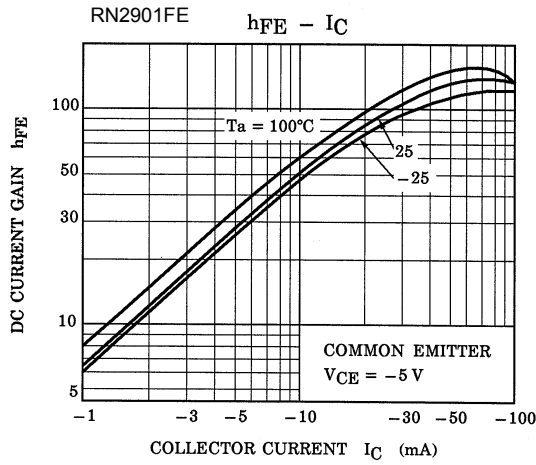


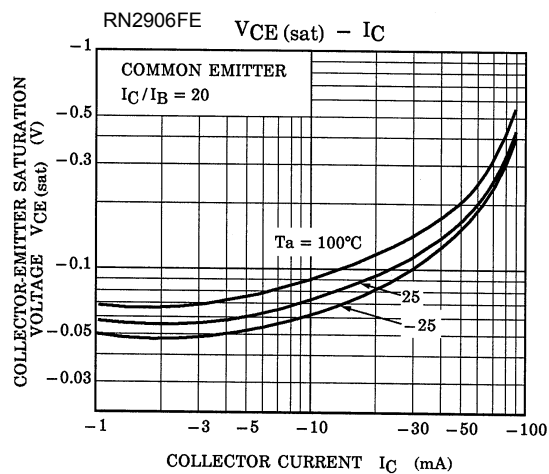
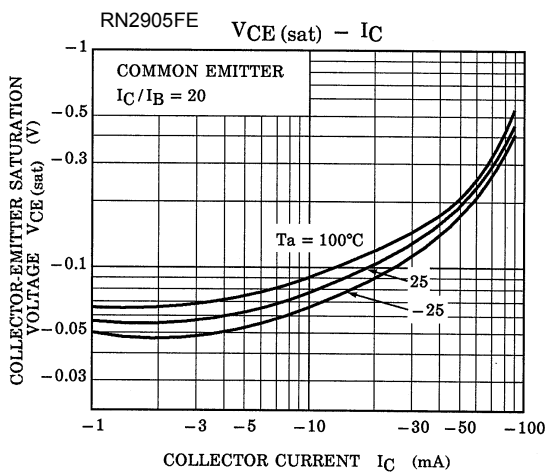
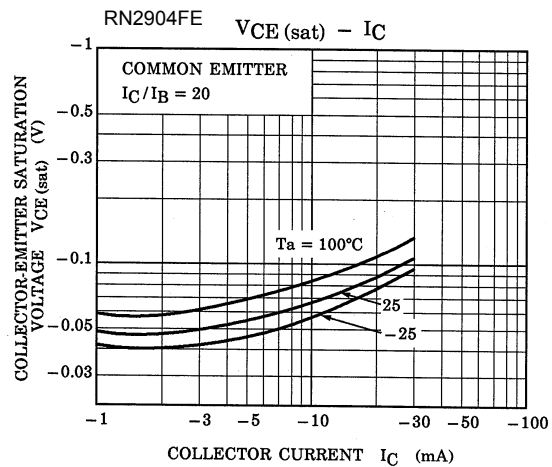
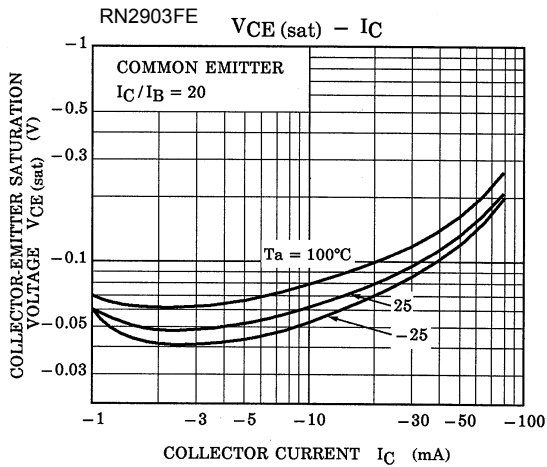
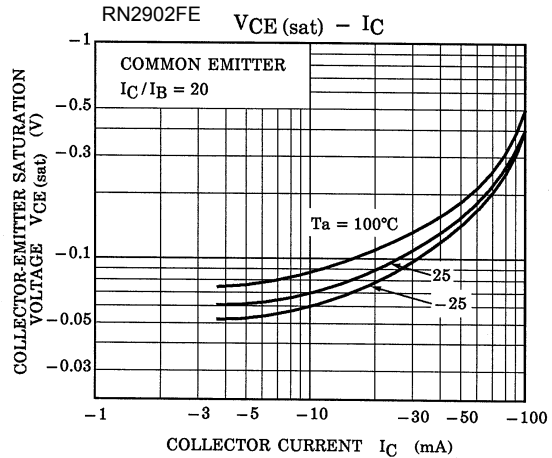
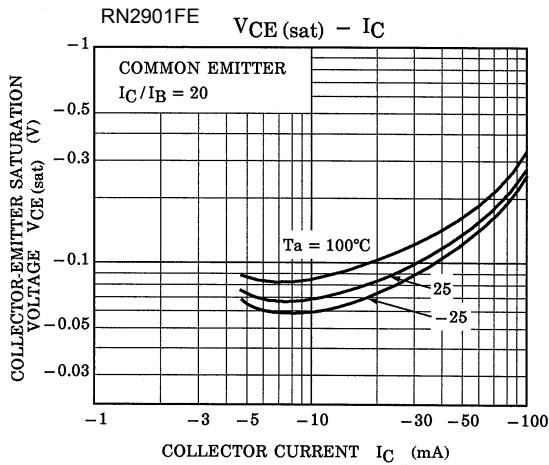
## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

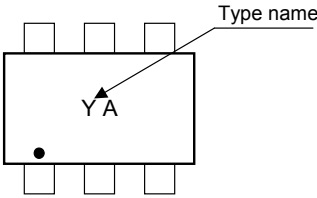
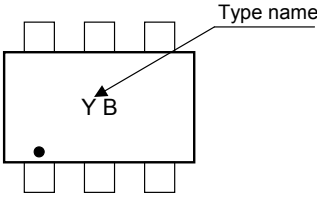
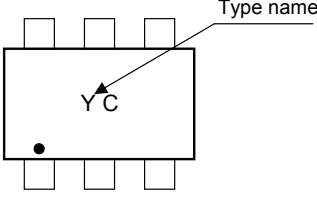
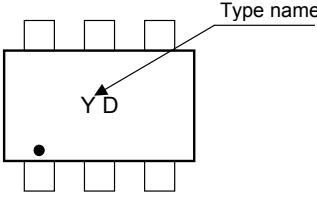
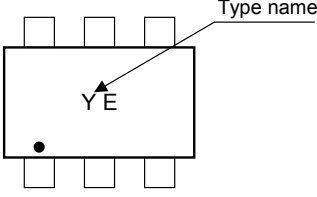
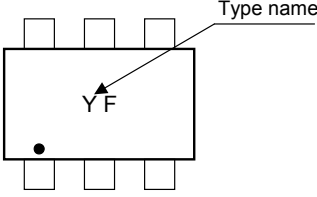
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2901FE~2906FE	$I_{CBO}$	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
		$I_{CEO}$	$V_{CE} = -50\text{ V}, I_B = 0$	—	—	-500	
Emitter cut-off current	RN2901FE	$I_{EBO}$	$V_{EB} = -10\text{ V}, I_C = 0$	-0.82	—	-1.52	mA
	RN2902FE			-0.38	—	-0.71	
	RN2903FE			-0.17	—	-0.33	
	RN2904FE			-0.082	—	-0.15	
	RN2905FE	$V_{EB} = -5\text{ V}, I_C = 0$	-0.078	—	-0.145		
	RN2906FE		-0.074	—	-0.138		
DC current gain	RN2901FE	$h_{FE}$	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	30	—	—	
	RN2902FE			50	—	—	
	RN2903FE			70	—	—	
	RN2904FE			80	—	—	
	RN2905FE			80	—	—	
	RN2906FE			80	—	—	
Collector-emitter saturation voltage	RN2901FE~2906FE	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	-0.1	-0.3	V
Input voltage (ON)	RN2901FE	$V_{I(ON)}$	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-1.1	—	-2.0	V
	RN2902FE			-1.2	—	-2.4	
	RN2903FE			-1.3	—	-3.0	
	RN2904FE			-1.5	—	-5.0	
	RN2905FE			-0.6	—	-1.1	
	RN2906FE			-0.7	—	-1.3	
Input voltage (OFF)	RN2901FE~2904FE	$V_{I(OFF)}$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-1.0	—	-1.5	V
	RN2905FE, 2906FE			-0.5	—	-0.8	
Transition frequency	RN2901FE~2906FE	$f_T$	$V_{CE} = -10\text{ V}, I_C = -5\text{ mA}$	—	200	—	MHz
Collector output capacitance	RN2901FE~2906FE	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF
Input resistor	RN2901FE	R1	—	3.29	4.7	6.11	k $\Omega$
	RN2902FE			7	10	13	
	RN2903FE			15.4	22	28.6	
	RN2904FE			32.9	47	61.1	
	RN2905FE			1.54	2.2	2.86	
	RN2906FE			3.29	4.7	6.11	
Resistor ratio	RN2901FE~2904FE	R1/R2	—	0.9	1.0	1.1	
	RN2905FE			0.0421	0.0468	0.0515	
	RN2906FE			0.09	0.1	0.11	









Type Name	Marking
RN2901FE	
RN2902FE	
RN2903FE	
RN2904FE	
RN2905FE	
RN2906FE	

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